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Jo Bryan

In Re Application of:

Confirmation No.: 4791

Gole, et al.

Examiner: To be assigned

Serial No. 10/633,259

Docket No. 62004-1683

Filing Date: August 1, 2003

Group Art Unit: 2812

For: Porous Gas Sensors and Method of Preparation Thereof

The following is a list of documents enclosed:

Return Postcard Information Disclosure Statement Form PTO-1449 (2 pages)

00079545

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of:

Gole, et al.

Confirmation No.: 4791

Examiner: To be assigned

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For: Porous Gas Sensors and Method of Preparation Thereof

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexanddria, Virginia 22313-1450

Sir:

This information disclosure statement is filed in accordance with 37 C.F.R. §§ 1.56, 1.97, and 1.98. Listed on the accompanying form PTO-1449 are documents which may or may not be considered material to the examination of this application. These documents were made of record in a prior application filed March 29, 2001 and having serial no. 09/820,412, and Patent No.: 6,589,883, to which priority is claimed relative to the present application pursuant to 35 U.S.C. §120. Copies of these documents are not being provided pursuant to 37 C.F.R. § 1.98(d)(1) and (2), which provides:

- (d) A copy of any patent, publication, pending U.S. application or other information, as specified in paragraph (a) of this section, listed in an information disclosure statement is required to be provided, even if the patent, publication, pending U.S. application or other information was previously submitted to, or cited by, the Office in an earlier application, unless:
 - (1) The application is properly identified in the information disclosure statement and is relied on for an earlier effective filing date under 35 U.S.C. §120; and
 - (2) The information disclosure statement submitted in the earlier application complies with a paragraphs (a) through (c) of this section.

The following rights are reserved by the Applicant(s): the right to establish the patentability of

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documents may not be enabling for the teachings they purport to offer.

This statement should not be construed as a representation that an exhaustive search has

been made, or that information more material to the examination of the present application does

not exist. The Examiner is specifically requested not to rely solely on the materials submitted

herewith. The Examiner is requested to conduct an independent and thorough review of the

documents, and to form independent opinions as to their significance.

It is respectfully requested that the Examiner initial and return a copy of the enclosed

PTO-1449 to indicate the documents have been considered.

Respectfully submitted,

THOMAS, KAYDEN, HORSTEMEYER

& RISLEY, L.L.P.

By:

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Docket: 62004-1683

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Form PTO-1449 OVERFORMATION DISCLOSURE CITATION							Attorney Docket No. 062004-1683 Applicant			Serial No. 10/633,259			
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